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Notice of Allowability	Application No.	Applicant(s)	71.
	10/791,599	WU et al.	
	Examiner	Art Unit	
	Lee, Calvin	2818	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED in this ap i) or other appropriate communication RIGHTS. This application is subject to	plication. If not include will be mailed in due	ed course. THIS
1. This communication is responsive to			
2. ☑ The allowed claim(s) is/are <u>1-20</u> .			
3. \boxtimes The drawings filed on <u>01 March 2004</u> are accepted by the	Examiner.		
 4. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some* c) None of the: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient. 6. CORRECTED DRAWINGS (as "replacement sheets") must be submitted. (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached			
Supervisory F	Paper No./Mail Da	(PTO-413), te ment/Comment	·

Application No: 10/791,599

Docket: 67200-1103

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OFFICE ACTION

Allowable Subject Matter

Claims 1-20 are allowed. Following is the examiner's reason for allowance:

The closest art, US 5,200,636 to *Uemura et al*, discloses a first polysilicon layer 28 formed on thermal oxide films 24, 25, 27 in regions of an EPROM memory cell and a MOSFET [Fig. 2F and col. 7]; and a closer art US 5,712,201 to *Lee et al* discloses a single level of polysilicon 15a for both a high capacity DRAM cell 1 and a CMOS logic cell 2 [Fig. 7 and col. 4]. None of the cited arts teaches, *inter alia*, forming a first portion of a dielectric layer overlying the polysïlicon portion while blocking oxide growth over the first active region and forming a gate dielectric layer over the exposed portions of the substrate in the first active region to a predetermined thickness while simultaneously forming a second portion of the dielectric layer over the second active region to form the dielectric layer at a final predetermined thickness.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance.

Contact Information

Any inquiry concerning this communication from the Examiner should be directed to *Calvin Lee* at (571) 272-1896 from 7:00AM to 5:00PM (Monday-Thursday, Eastern Time). If attempts to reach the examiner by telephone are unsuccessful, Art Unit 2825's Supervisory Patent Examiner *David C. Nelms* can be reached at (571) 272-1787.

Any inquiry relating to the status of this application should be directed to the Group receptionist whose telephone number is (703) 308-0596. The central fax number is (703) 872-9306 for all communications to be entered (e.g., amendments, remarks, IDS, etc.)

Dated: August 22, 2005

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David Nelms Supervisory Patent Examiner Technology Center 2800